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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/673,326	09/30/2003	Chi-Shen Lee	LEEC3075/EM	2258	
23364 7:	590 06/28/2006		EXAMINER		
BACON & THOMAS, PLLC			MCPHERSON, JOHN A		
625 SLATERS FOURTH FLO		ART UNIT	PAPER NUMBER		
ALEXANDRIA, VA 22314			1756		
			DATE MAILED: 06/28/2006	`	

Please find below and/or attached an Office communication concerning this application or proceeding.

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Office Action Summary		10/673,3	26	LEE ET AL.	
		Examine	r	Art Unit	
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A SH WHIC - Exter after - If NO - Failu Any	ORTENED STATUTORY PERIOD F CHEVER IS LONGER, FROM THE M nsions of time may be available under the provisions SIX (6) MONTHS from the mailing date of this comm o period for reply is specified above, the maximum sta re to reply within the set or extended period for reply reply received by the Office later than three months a ed patent term adjustment. See 37 CFR 1.704(b).	IAILING DATE OF TI of 37 CFR 1.136(a). In no ex nunication. atutory period will apply and v will, by statute, cause the ap	HIS COMMUNICATION rent, however, may a reply be tim rill expire SIX (6) MONTHS from blication to become ABANDONE	I. ely filed the mailing date of this co (35 U.S.C. § 133).	
Status					
2a) <u></u> 3) <u></u>	Since this application is in condition closed in accordance with the practi	2b)⊠ This action is r for allowance excep	non-final. t for formal matters, pro		e merits is
Dispositi	on of Claims				
5) □ 6) ⋈ 7) ⋈ 8) □ Applicati 9) □ 10) ⋈	Claim(s) 1-10 is/are pending in the a 4a) Of the above claim(s) is/a Claim(s) is/are allowed. Claim(s) 1-10 is/are rejected. Claim(s) 8 is/are objected to. Claim(s) are subject to restriction Claim(s) are subject to restr	e Examiner. er 2003 is/are: a) ction to the drawing(s)	requirement. accepted or b) object be held in abeyance. See red if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CF	FR 1.121(d).
	•	o by the Examiner. It	oto the attached office		0 102.
12)⊠ a)[Acknowledgment is made of a claim All b) Some * c) None of: 1. Certified copies of the priority 2. Certified copies of the priority 3. Copies of the certified copies application from the Internation	documents have been documents have been of the priority documental Bureau (PCT Ru	en received. en received in Application ents have been receive le 17.2(a)).	on No ed in this National	Stage
2) Notice 3) Information	t(s) se of References Cited (PTO-892) se of Draftsperson's Patent Drawing Review (P mation Disclosure Statement(s) (PTO-1449 or or No(s)/Mail Date		4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	te	D-152)

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DETAILED ACTION

Drawings

1. The drawings are objected to as failing to comply with 37 CFR 1.84(p)(5) because they include the following reference character(s) not mentioned in the description: 50, 40, 31, 41, 51, 42, 52, 32, 63, 64, 65, 71 and 72 (see Figures 1b-j). Corrected drawing sheets in compliance with 37 CFR 1.121(d), or amendment to the specification to add the reference character(s) in the description in compliance with 37 CFR 1.121(b) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Claim Objections

2. Claim 8 is objected to under 37 CFR 1.75(c), as being of improper dependent form for failing to further limit the subject matter of a previous claim. Applicant is required to cancel the claim(s), or amend the claim(s) to place the claim(s) in proper dependent form.

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Claim 8 presents the limitation "wherein said method forming for the first metal wiring layer can be a selective deposition method, and the selective deposition method uses the selective conducting wiring layout to deposit the metal on the right position", however claim 1 already requires this limitation in lines 9-11.

Claim Rejections - 35 USC § 112

3. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-10 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1 recites the limitation "the first masking process" in lines 5-6. There is insufficient antecedent basis for this limitation in the claim.

Claim 1 recites the limitation "the wiring layout" in lines 10-11. There is insufficient antecedent basis for this limitation in the claim.

Claim 1 recites the limitation "the second masking process" in line 14. There is insufficient antecedent basis for this limitation in the claim.

Claim 1 recites the limitation "the contact window" in lines 14-15. There is insufficient antecedent basis for this limitation in the claim.

Claim 1 recites the limitation "the third masking process" in line 16. There is insufficient antecedent basis for this limitation in the claim.

Claim 1 recites the limitation "the second metal wiring layer" in lines 17-18.

There is insufficient antecedent basis for this limitation in the claim.

Regarding claim 4, the phrase "such as" (line 4) renders the claim indefinite because it is unclear whether the limitations following the phrase are part of the claimed invention. See MPEP § 2173.05(d).

Claim 4 presents the limitation "wherein the deposition process can be against of multi-layer materials and structural layers induced from metal materials such as diffusion, and adhesion before the step of forming the first metal wire". However, it is unclear what Applicant intends by "against of multi-layer materials and structural layers induced from metal materials such as diffusion, and adhesion before the step of forming the first metal wire" as it relates to the deposition process of the present invention.

Specifically, this limitation does not appear to describe a deposition process.

Regarding claim 5, the phrase "such as" (line 5) renders the claim indefinite because it is unclear whether the limitations following the phrase are part of the claimed invention. See MPEP § 2173.05(d).

Claim 5 presents the limitation "wherein said second metal wires can be Al, Cu, Ag, Mo, Cr, Ti, or W as well as low-resistance metals, other alloy materials, or the induced material such as diffusion, and adhesion with multi-layer structure of the metal material". However, it is unclear what Applicant intends by "or the induced material such as diffusion, and adhesion with multi-layer structure of the metal material" as it relates to the second metal wires. Specifically, this limitation does not appear to describe the composition of the second metal wires.

Claim 6 recites the limitation "the forth masking process" in line 4. There is insufficient antecedent basis for this limitation in the claim.

Claim 9 presents the limitation "wherein the A-Si layer can be made of A-Si, or poly-Si materials". However, it is unclear what Applicant intends by this statement, because it appears that an A-Si (amorphous silicon) layer must be made of A-Si, and that it could not be made of poly-Si (polycrystalline silicon).

Claim 10 presents the limitation "wherein the passivation layer can be made of SiO₂, silicon nitride, or other <u>organic</u> materials. However, SiO₂ and silicon nitride are inorganic materials, not organic materials. Accordingly, is not clear if organic materials are within the scope of this claim.

Pertinent Prior Art

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

US 6,822,702 discloses a method of forming an active plate for a liquid crystal display comprising the steps of forming source and drain conductors, pixel electrodes and column electrodes by depositing and patterning a transparent conductive layer; and selectively plating areas of the transparent conductor layer to form a metallic layer for reducing the resistivity of the transparent conductive layer.

US 2002/0093600 discloses a method of fabricating an array substrate for a liquid crystal display device comprising the steps of forming a first metal layer on a substrate, forming a gate line and a gate electrode, forming a gate insulation layer to

cover the first metal layer, forming a pure amorphous silicon layer and a doped amorphous silicon layer on the gate insulation layer, forming an ohmic contact layer and an active layer over the gate electrode, forming a transparent conductive material on the gate insulation layer to cover the active layer and the ohmic contact layer, forming a photoresist layer on the transparent conductive material, patterning the photoresist layer using a mask, forming a data line, a pixel electrode, a source electrode and a drain electrode, and forming a second metal layer on an entire surface of the data line.

US 5,663,575 discloses method of forming a liquid crystal display comprising the steps of providing a transparent conductive electrode as a lower electrode of a gate line and a storage capacitor, wherein the transparent conductive electrode has a plurality of sections removed so as to form a ladder or mesh structure, and depositing an anodic oxidative metal on the whole surface of the transparent conductive film after forming a gate electrode.

Allowable Subject Matter

- 5. Claims 1-10 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. 112, 2nd paragraph, set forth in this Office action.
- 6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to John A. McPherson whose telephone number is (571) 272-1386. The examiner can normally be reached on Monday through Friday, 8:00 AM to 4:30 PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark Huff can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571,272-1000.

> John A. McPherson **Primary Examiner** Art Unit 1756

JAM 6/21/06